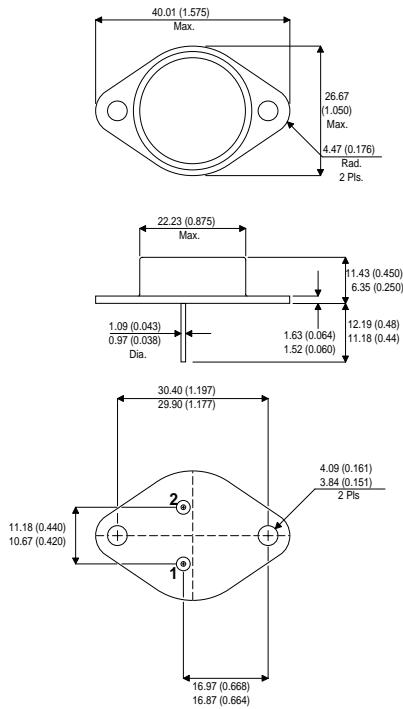


**MECHANICAL DATA**

Dimensions in mm(inches)



**TO3**

PIN 1 — Base      PIN 2 — Emitter      Case is Collector.

**PNP SILICON EPITAXIAL BASE  
POWER TRANSISTORS**

**APPLICATIONS**

Linear Power and Switching Applications

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CBO}$	Collector – Base Voltage ( $I_E = 0$ )	80V
$V_{CEO(sus)}$	Collector – Emitter Voltage ( $I_B = 0$ )	80V
$V_{EBO}$	Emitter – Base Voltage ( $I_C = 0$ )	7V
$I_C$	Collector Current	10A
$I_B$	Base Current	4A
$P_{TOT}$	Total Power Dissipation at $T_{case} = 25^{\circ}C$	150W
$T_{stg}$	Storage Temperature	65 to 200°C
$T_j$	Junction Temperature	200°C

**THERMAL CHARACTERISTICS**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.17 °C/W
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**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CEO(sus)^*}$ Collector - Emitter Sustaining Voltage	$I_C = 200mA$ $I_B = 0$	-80			V
$V_{CE(sat)^*}$ Collector - Emitter Saturation Voltage	$I_C = 5A$ $I_B = 0.5V$	-1			
$V_{BE(on)^*}$ Base Emitter Voltage	$I_C = 5A$ $V_{CC} = 2V$			1.8	V
	$I_C = 10A$ $V_{CC} = 4V$			4	
$I_{EBO}$ Emmiter Cut-off Current	$I_C = 0$ $V_{EB} = 7V$			-5	mA
$I_{CEX}$ Collector Cut-off Current	$V_{BE} = 1.5V$ $V_{CE} = 80$ $T_c = 150^{\circ}C$			-1	mA
				-5	
$h_{FE}^*$ DC Current Gain	$I_C = 1A$ $V_{CE} = 2V$	50		150	—
	$I_C = 3A$ $V_{CE} = 2V$	30		120	
	$I_C = 10A$ $V_{CE} = 4V$	5			
$f_t$ Transition Frequency	$I_C = 0.5A$ $V_{CE} = 10V$ $f = 1.MHz$	4			MHz

\* Pulsed duration = 300  $\mu s$ , duty cycle = 1.5%